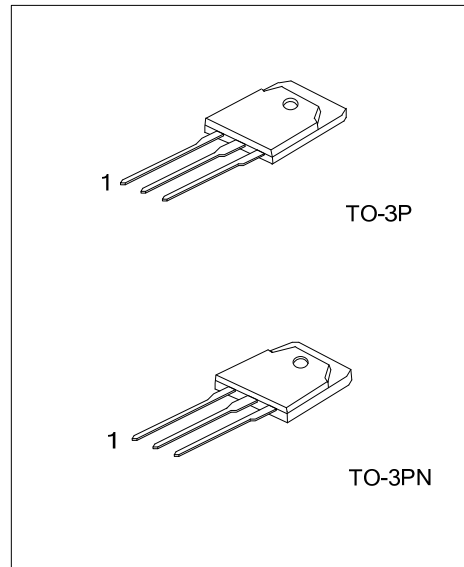




## 2SC4467

## NPN EPITAXIAL SILICON TRANSISTOR

### SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR



#### DESCRIPTION

The UTC **2SC4467** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4467** is suitable for audio and general purpose, etc.

#### FEATURES

- \* High DC current gain
- \* High collector-base breakdown voltage

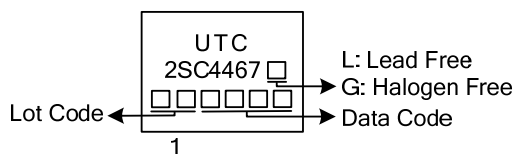
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4467L-x-T3P-T	2SC4467G-x-T3P-T	TO-3P	B	C	E	Tube
2SC4467L-x-T3N-T	2SC4467G-x-T3N-T	TO-3PN	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SC4467L-x-T3P-T</p>	<p>(1) T: Tube (2) T3P: TO-3P, T3N: TO-3PN (3) x: reference to Classification of <math>h_{FE}</math> (4) L: Lead Free, G: Halogen Free and Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	120	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	8	A
Base Current	I <sub>B</sub>	3	A
Collector Power Dissipation (T <sub>C</sub> =25°C)	P <sub>C</sub>	80	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

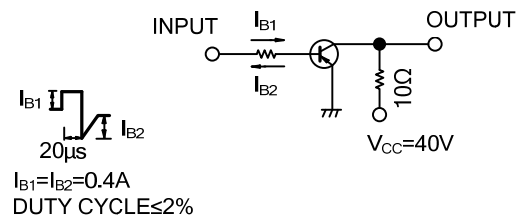
■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =160V			10	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =6V			10	μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =50mA	120			V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =3A	50			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =3A, I <sub>B</sub> =0.3A			1.5	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =12V, I <sub>E</sub> =-0.5A		20		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		200		pF
Switching time	Turn-on time	V <sub>CC</sub> =40V, R <sub>L</sub> =10Ω, I <sub>C</sub> =4A, I <sub>B1</sub> =0.4A I <sub>B2</sub> =0.4A		0.13		μS
	Storage time			3.50		μS
	Fall time			0.32		μS

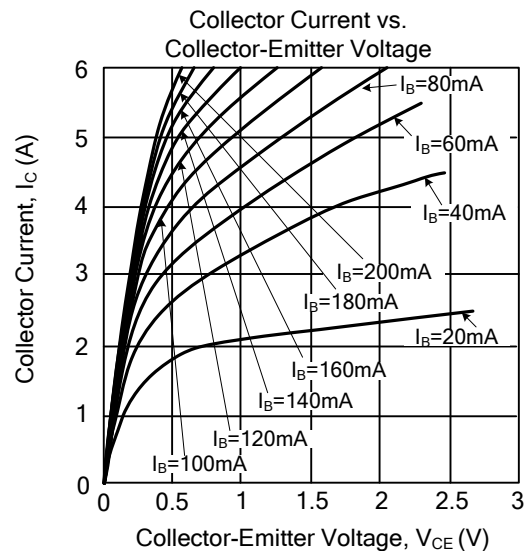
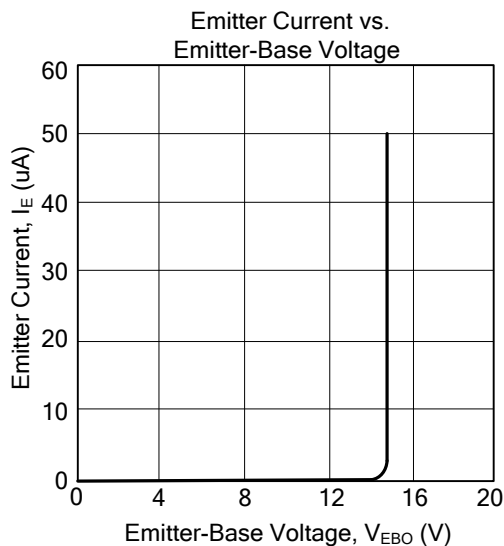
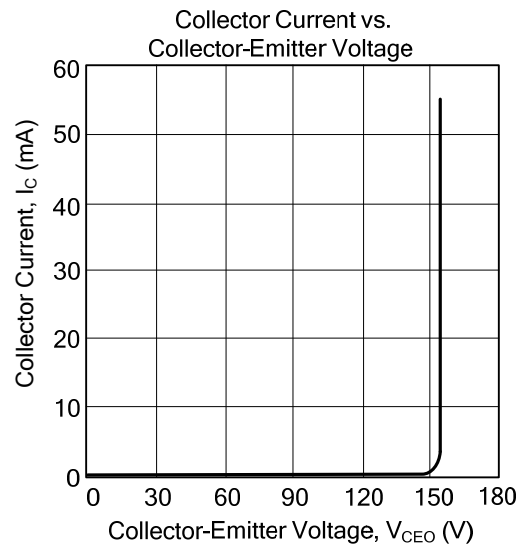
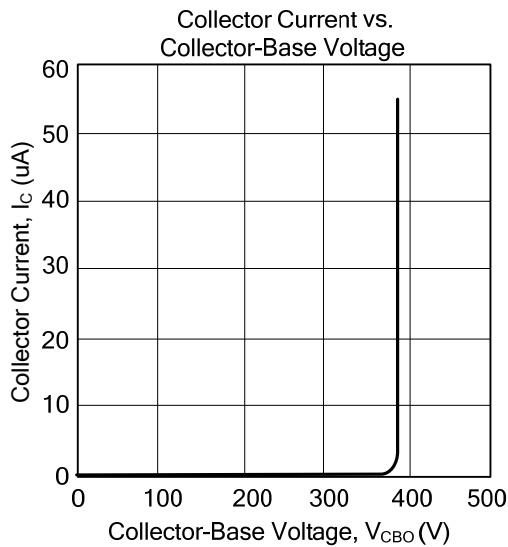
■ CLASSIFICATION OF h<sub>FE</sub>

RANK	O	P	Y
RANGE	50~100	70~140	90~180

### ■ TEST CIRCUIT



## TYPICAL CHARACTERISTICS



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